## **BAV74LT1G**

## Monolithic Dual Switching Diode

#### **Features**

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	Vdc
Forward Current	l <sub>F</sub>	200	mAdc
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

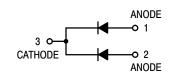
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



## ON Semiconductor®

#### www.onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 9

#### **MARKING DIAGRAM**



JA = Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BAV74LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAV74LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### BAV74LT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage $(I_{(BR)} = 5.0 \mu Adc)$	V <sub>(BR)</sub>	50	-	Vdc
Reverse Voltage Leakage Current, (Note 3) (V <sub>R</sub> = 50 Vdc, T <sub>J</sub> = 125°C) (V <sub>R</sub> = 50 Vdc)	I <sub>R</sub>	- -	100 0.1	μAdc
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	C <sub>D</sub>	-	2.0	pF
Forward Voltage (I <sub>F</sub> = 100 mAdc)	V <sub>F</sub>	-	1.0	Vdc
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mAdc, I <sub>R(REC)</sub> = 1.0 mAdc, measured at I <sub>R</sub> = 1.0 mA, R <sub>L</sub> = 100 $\Omega$ )	t <sub>rr</sub>	_	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while the second diode is unbiased.

## **CURVES APPLICABLE TO EACH ANODE**

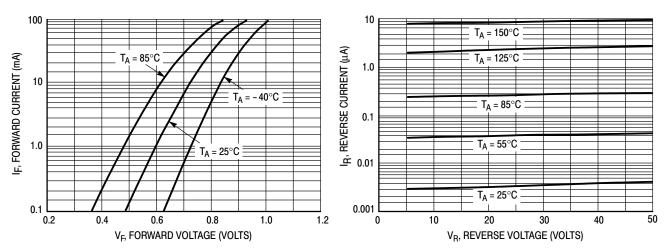


Figure 1. Forward Voltage

Figure 2. Leakage Current

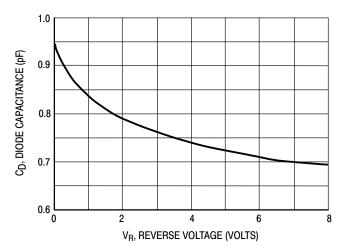


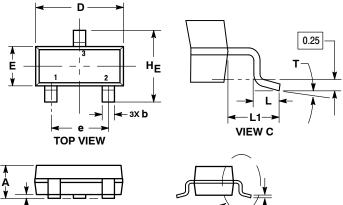
Figure 3. Capacitance



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1



SEE VIEW C

**END VIEW** 

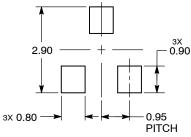
#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
T	0°		10°	0°		10°	

#### **RECOMMENDED SOLDERING FOOTPRINT**

SIDE VIEW



2. ANODE

STYLE 27: PIN 1. CATHODE 2. CATHODE

3. CATHODE

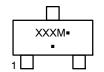
DIMENSIONS: MILLIMETERS

2. SOURCE

STYLE 28: PIN 1. ANODE 2. ANODE

3. ANODE

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

STYLE 13: PIN 1. SOURCE

2. DRAIN

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ON
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	

3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE

2. CATHODE

2. CATHODE

PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	NO CONNECTION	PIN 1.	NO CONNECTION	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	CATHODE	2.	CATHODE	2.	ANODE	2.	CATHODE	2.	ANODE	2.	ANODE
3.	ANODE	3.	CATHODE	3.	CATHODE	3.	ANODE	3.	CATHODE-ANODE	3.	GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
<ol><li>DRAIN</li></ol>	<ol><li>INPUT</li></ol>	<ol><li>CATHODE</li></ol>	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

Γ		SOT-23 (TO-236)		PAGE 1 OF 1
	DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED O	

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

STYLE 14: PIN 1. CATHODE

2. GATE

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability. arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthnotized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

**TECHNICAL SUPPORT** 

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative